

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising  
a first transistor and a second transistor formed on  
a semiconductor substrate, wherein a gate side wall of  
the second transistor has a thickness equal to that of  
a gate side wall of the first transistor, wherein each  
of the first and second transistors has an inner low  
impurity diffusion region and an outer high impurity  
diffusion region, and wherein the size of the inner low  
impurity diffusion region of the second transistor  
along the surface of the semiconductor substrate is  
larger than that of the inner low impurity diffusion  
region of the first transistor.

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